



# Product data sheet

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Feature





Semiconductor



### 44W peak pulse power per line ( $t_P = 8/20 \mu s$ )

- SOD-923 package
- Replacement for MLV(0402)
- Bidirectional configurations
- Response time is typically < 1ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to
- IEC61000-4-4 (EFT) 40A (5/50ns)

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260  $^\circ\!\mathrm{C}$
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil



SOD-923

#### Electrical characteristics per line@25°C (unless otherwise specified)

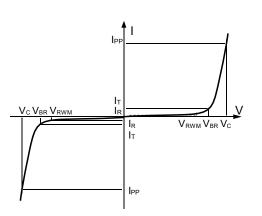
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				3.3	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> = 1mA	5			V
Reverse Leakage Current	I <sub>R</sub>	<b>V<sub>RWM</sub> = 5V Т=25</b> ℃			2.5	μA
Maximum Reverse Peak Pulse Current	I <sub>PP</sub>			2.3		А
Clamping Voltage	Vc	Ipp MAX, tp =8/20 µ s			19	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		12	18	pF

#### Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t <sub>p</sub> =8/20µs)	P <sub>pp</sub>	44	W
Operating Temperature	TJ	-55 to +150	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

#### **Electronics Parameter**

Symbol	Parameter		
V <sub>RWM</sub>	Peak Reverse Working Voltage		
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>		
V <sub>BR</sub>	Breakdown Voltage @ I⊤		
Ι <sub>Τ</sub>	Test Current		
IPP	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P <sub>PP</sub>	Peak Pulse Power		
С」	Junction Capacitance		
lF	Forward Current		
VF	Forward Voltage @ I <sub>F</sub>		

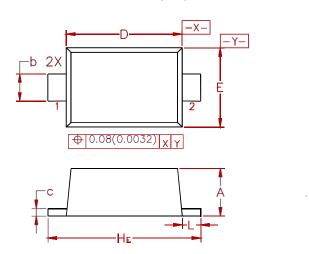




MSESD9B3.3ST5G

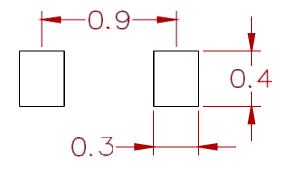
.3ST5G HF Semiconductor Compiance

#### PACKAGE MECHANICAL DATA



Dim	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
Α	0.36	0.40	0.43	0.014	0.016	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
HE	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

#### Suggested Pad Layout



**Dimensions: Millimeters** 

#### **REEL SPECIFICATION**

P/N	PKG	QTY
MSESD9B3.3ST5G	SOD-923	8000



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